

Description

The SI2301 is the high cell density trenched P-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

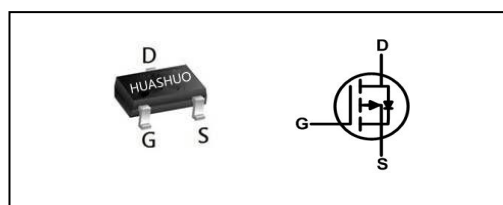
The SI2301 meet the RoHS and Green Product requirement with full function reliability approved.

- Green Device Available
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	-20	V
$R_{DS(ON),typ}$	130	mΩ
I_D	-2	A

SOT23 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-2	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-1.4	A
I_{DM}	Pulsed Drain Current ²	-8	A
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	145	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	80	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-2A	---	130	150	mΩ
		V _{GS} =-2.5V, I _D =-1A	---	170	190	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.3	-0.65	-1.0	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-16V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-16V, V _{GS} =0V, T _J =55°C	---	---	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ± 12V, V _{DS} =0V	---	---	± 100	nA
g _f	Forward Transconductance	V _{DS} =-5V, I _D =-1A	---	5	---	S
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-2A	---	4.3	---	nC
Q _{gs}	Gate-Source Charge		---	0.7	---	
Q _{gd}	Gate-Drain Charge		---	1	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-10V, V _{GS} =-4.5V, R _G =3.3Ω I _D =-2A	---	12	---	ns
T _r	Rise Time		---	20	---	
T _{d(off)}	Turn-Off Delay Time		---	23	---	
T _f	Fall Time		---	9	---	
C _{iss}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	---	270	---	pF
C _{oss}	Output Capacitance		---	54	---	
C _{rss}	Reverse Transfer Capacitance		---	44	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	-2	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch²FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

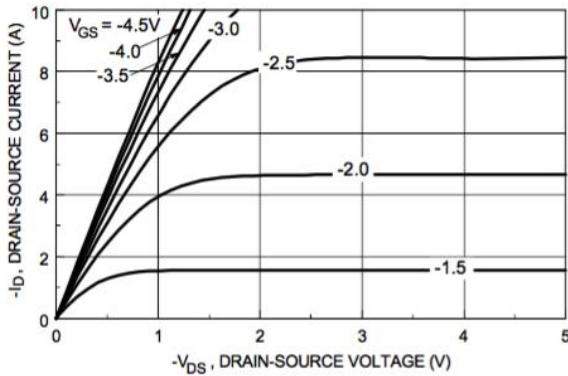


Figure 1. On-Region Characteristics.

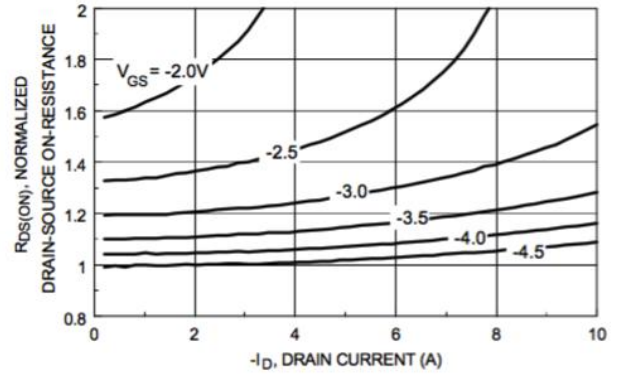


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

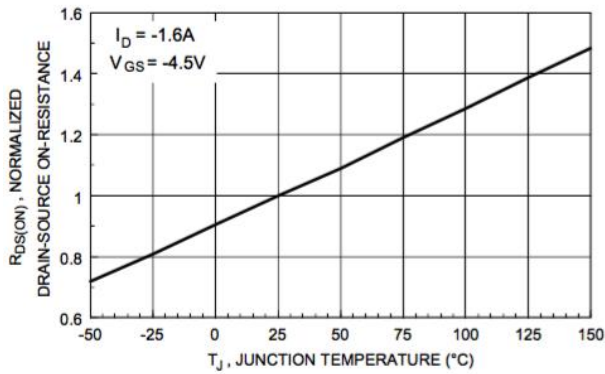


Figure 3. On-Resistance Variation with Temperature.

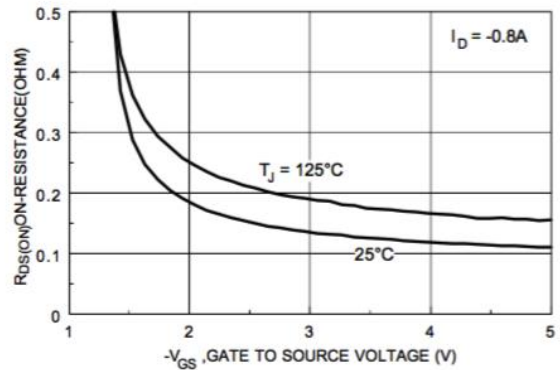


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

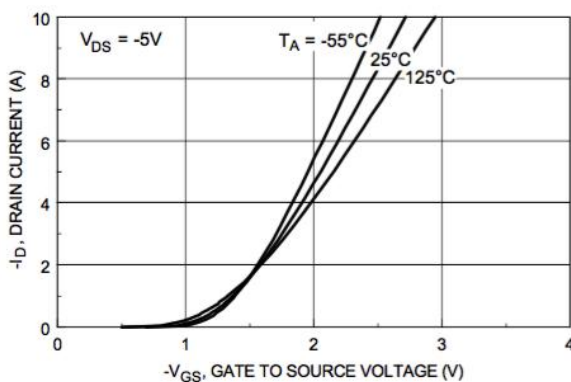


Figure 5. Transfer Characteristics.

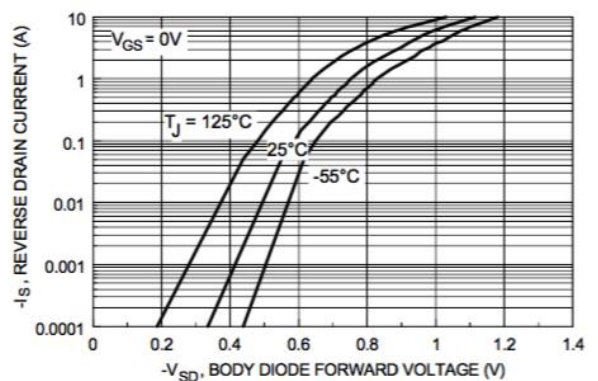


Figure 6 . Body Diode Forward Voltage Variation with Source Current and Temperature.



P-Ch 20V Fast Switching MOSFETs

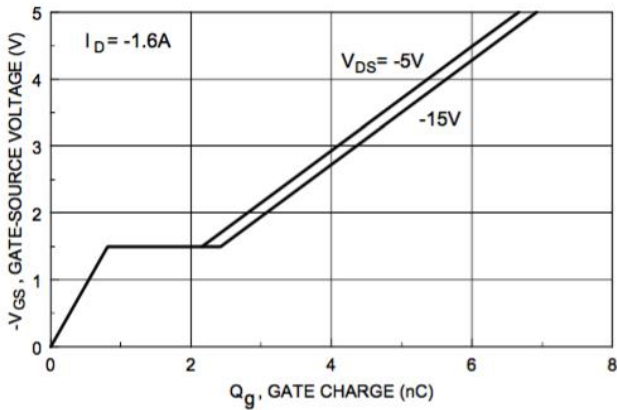


Figure 7. Gate Charge Characteristics.

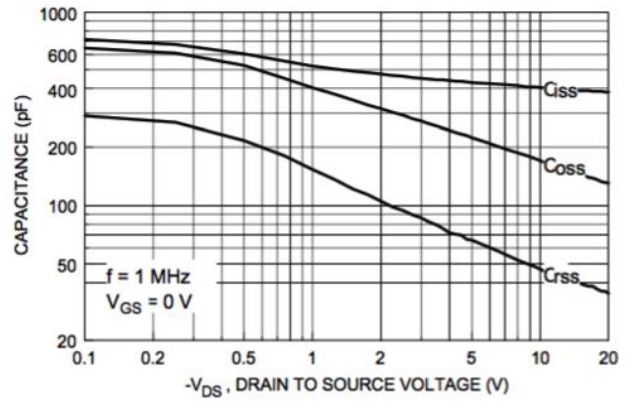


Figure 8. Capacitance Characteristics.

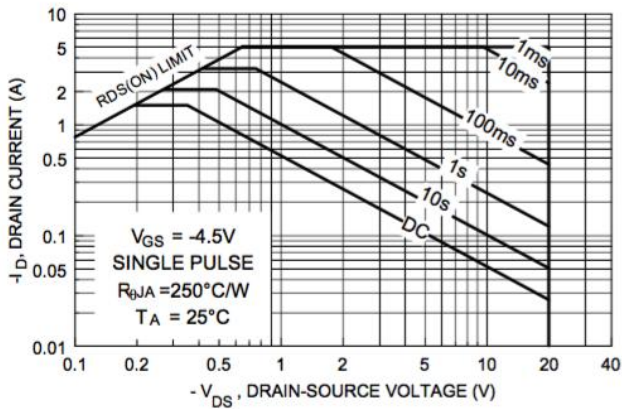


Figure 9. Maximum Safe Operating Area.

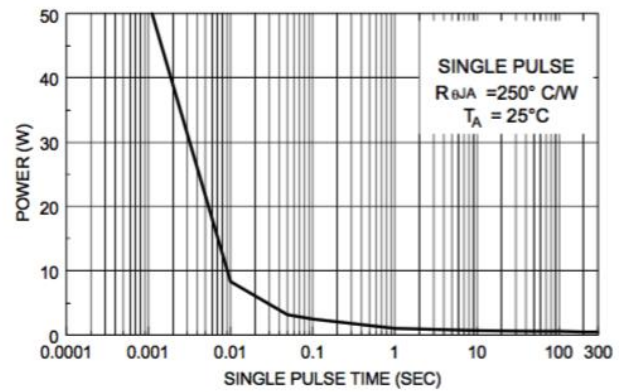


Figure 10. Single Pulse Maximum Power Dissipation.

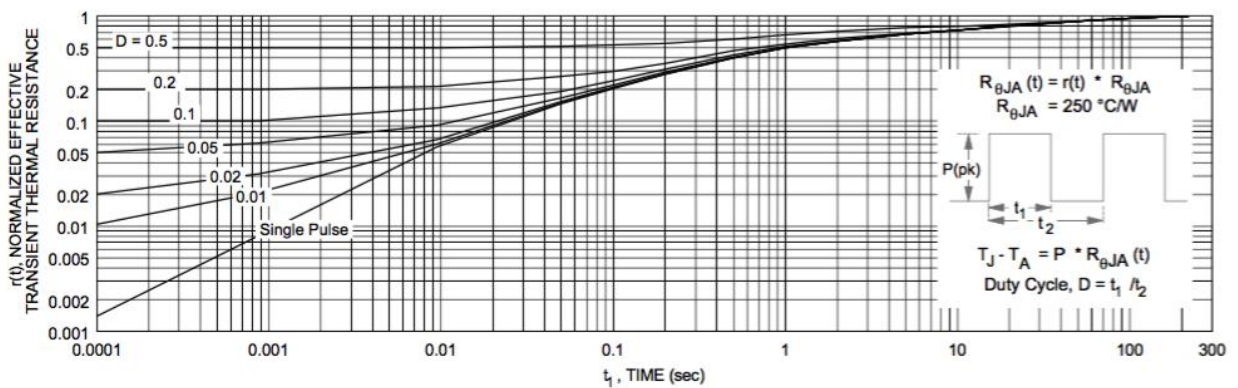
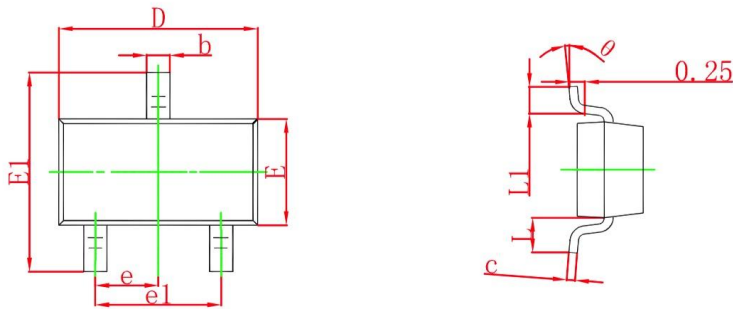


Figure 11. Transient Thermal Response Curve.

Ordering Information

Part Number	Package code	Packaging
SI2301	SOT-23	3000/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

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